



Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 116434		APPLICATION NO. 10/614,985	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Susumu INOUE			
				FILING DATE July 9, 2003		2813	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
CC	1	US 6,255,166 B1	07/03/2001	Ogura et al.	438	257	
CC	2	5,408,115	04/18/1995	Chang	257	324	
CC	3	5,969,383	10/19/1999	Chang et al.	257	316	
CC	4	5,422,504	06/06/1995	Chang et al.	257	321	
CC	5	5,494,838	02/27/1996	Chang et al.	438	267	
CC	6	US 6,177,318 B1	01/23/2001	Ogura et al.	438	258	
CC	7	US 6,248,633 B1	06/19/2001	Ogura et al.	438	267	
CC	8	10/636,582 Attorney Docket 116815	08/08/2003	Inoue			
CC	9	10/636,562 Attorney Docket 116817	08/08/2003	Inoue			
CC	10	10/689,990 Attorney Docket 117588	10/22/2003	Kasuya			
CC	11	10/636,581 Attorney Docket 116816	08/08/2003	Yamamukai			
CC	12	10/690,025 Attorney Docket 117576	10/22/2003	Kasuya			
CC	13	10/689,993 Attorney Docket 117577	10/22/2003	Kasuya			
CC	14	10/689,987 Attorney Docket 117575	10/22/2003	Kasuya			
CC	15	10/244,627 Attorney Docket 113761	09/17/2002	Ebina et al.			
CC	16	10/234,197 Attorney Docket 113668	09/05/2002	Ebina et al.			
CC	17	10/339,555 Attorney Docket 114656	01/10/2003	Shibata			
CC	18	10/350,010 Attorney Docket 114766	01/24/2003	Kasuya			
CC	19	10/349,943 Attorney Docket 114765	01/24/2003	Kasuya			
CC	20	10/234,095 Attorney Docket 113669	09/05/2002	Ebina et al.			
CC	21	10/052,255 Attorney Docket 111778	01/23/2002	Ebina et al.			
CC	22	10/052,549 Attorney Docket 111779	01/23/2002	Ebina et al.			
CC	23	10/244,623 Attorney Docket 113760	09/17/2002	Ebina et al.			
CC	24	10/350,075 Attorney Docket 114768	01/24/2003	Kasuya			
CC	25	10/342,307 Attorney Docket 114425	01/15/2003	Ueda			
CC	26	10/349,958 Attorney Docket 114767	01/24/2003	Kasuya			
CC	27	10/339,558 Attorney Docket 114655	01/10/2003	Inoue			

Date: December 8, 2003



FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS. SUB CLASS
CC	28	JP B1 2978477 w/trans.	09/10/1999	Japan	
CC	29	JP A 7-161851 w/abstr. + trans.	06/23/1995	Japan	
CC	30	JP A 2001-156188 w/abstr. + trans.	06/08/2001	Japan	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)					
CC	31	Hayashi et al., "Twin MONOS Cell with Dual Control Gates," IEEE Symposium on VLSI Technology Digest of Technical Papers, 2000			
CC	32	Chang et al., "A New SONOS Memory Using Source-Side Injection for Programming," IEEE Electron Device Letters, Vol. 19, No. 7, pp. 253-255, July 1998.			
CC	32	Chen et al., "A Novel Flash Memory Device with S Plit Gate Source Side Injection and ONO Charge Storage Stack (SPIN)," Symposium on VLSI Technology Digest of Technical Papers, pp. 63-64, 1997			
EXAMINER		C. Chaudhari		DATE CONSIDERED 5-04	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

Date: December 8, 2003



Sheet 1 of 1

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
CC	1	6,413,821	07/02/2002	Ebina et al.	438	258	
CC	2	6,518,124	02/11/2003	Ebina et al.	438	258	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
EXAMINER C. Chaudhari				DATE CONSIDERED 5-04			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: January 22, 2004